Silicon Carbide Schottky Diode

1200 V, 8 A

FFSD08120A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

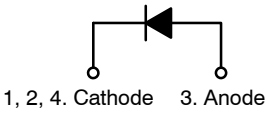
- Max Junction Temperature 175°C
- Avalanche Rated 80 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb−Free, Halogen Free/BFR Free and RoHS Compliant

Applications

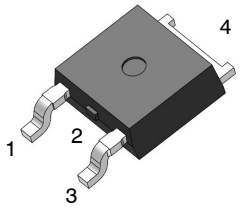
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

ON Semiconductor®

www.onsemi.com

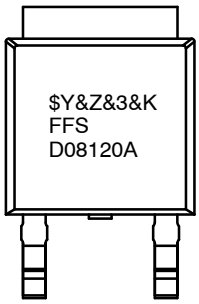


Schottky Diode



DPAK3
CASE 369AS

MARKING DIAGRAM



$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FFSD08120A	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

© Semiconductor Components Industries, LLC, 2017

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		1200	V
E_{AS}	Single Pulse Avalanche Energy (Note 1)		80	mJ
I_F	Continuous Rectified Forward Current @ T_C < 168°C		8	A
	Continuous Rectified Forward Current @ T_C < 135°C		22.5	A
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	T_C = 25°C, 10 μs	530	A
		T_C = 150°C, 10 μs	480	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	Half−Sine Pulse, t_p = 8.3 ms	77	A
$I_{F,RM}$	Repetitive Forward Surge Current	Half−Sine Pulse, t_p = 8.3 ms	45	A
P_{TOT}	Power Dissipation	T_C = 25°C	263	W
		T_C = 150°C	44	W
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 80 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 18 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.57	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_F	Forward Voltage	I_F = 8 A, T_C = 25°C	–	1.45	1.75	V
		I_F = 8 A, T_C = 125°C	–	1.7	2.0	
		I_F = 8 A, T_C = 175°C	–	2.0	2.4	
I_R	Reverse Current	V_R = 1200 V, T_C = 25°C	–	–	200	μA
		V_R = 1200 V, T_C = 125°C	–	–	300	
		V_R = 1200 V, T_C = 175°C	–	–	400	
Q_C	Total Capacitive Charge	V = 800 V	–	55	–	nC
C	Total Capacitance	V_R = 1 V, f = 100 kHz	–	538	–	pF
		V_R = 400 V, f = 100 kHz	–	50	–	
		V_R = 800 V, f = 100 kHz	–	40	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSD08120A	FFSD08120A	DPAK3	Tape & Reel†	13″	12 mm	2500 Units

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

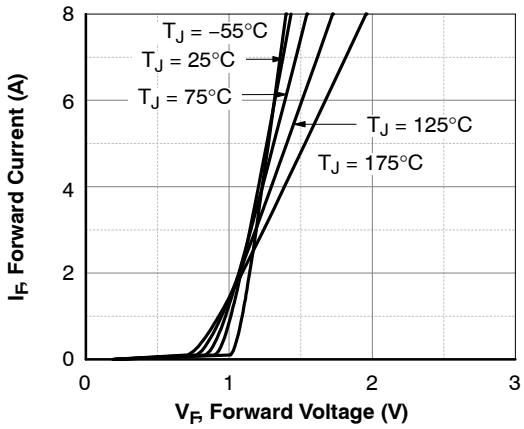


Figure 1. Forward Characteristics

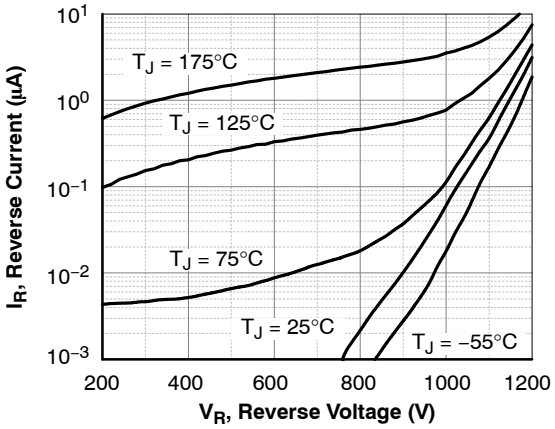


Figure 2. Reverse Characteristics

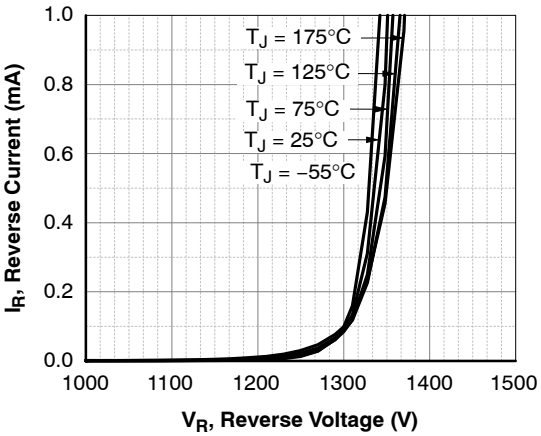


Figure 3. Reverse Characteristics

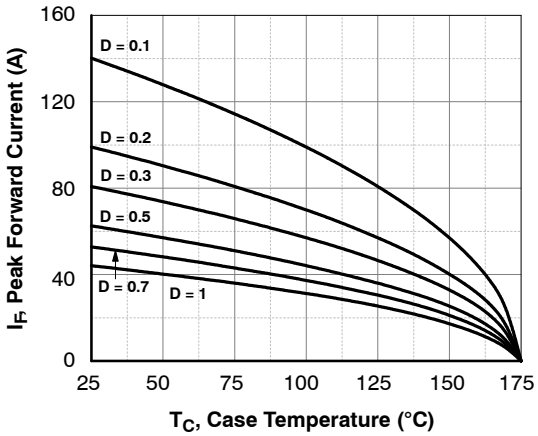


Figure 4. Current Derating

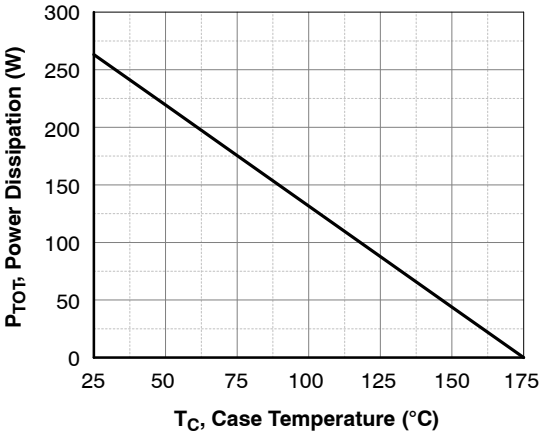


Figure 5. Power Derating

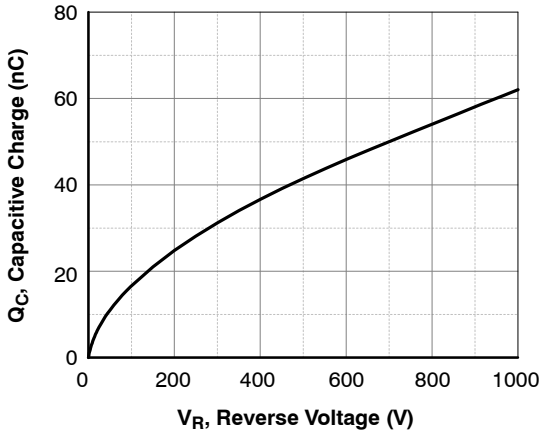


Figure 6. Capacitive Charge vs. Reverse Voltage

TYPICAL CHARACTERISTICS (Continued)

(T_J = 25°C unless otherwise noted)

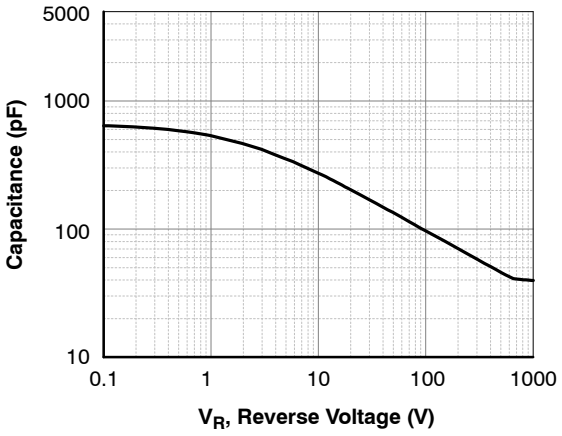


Figure 7. Capacitance vs. Reverse Voltage

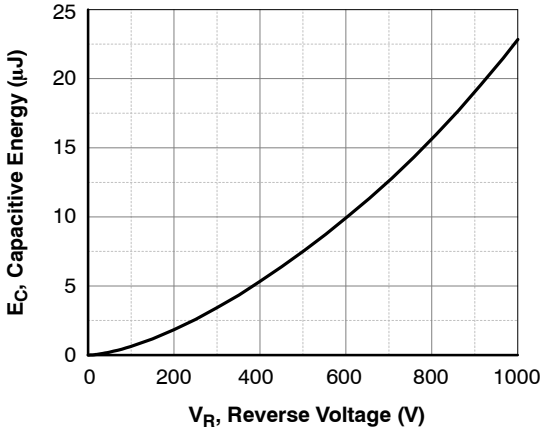


Figure 8. Capacitance Stored Energy

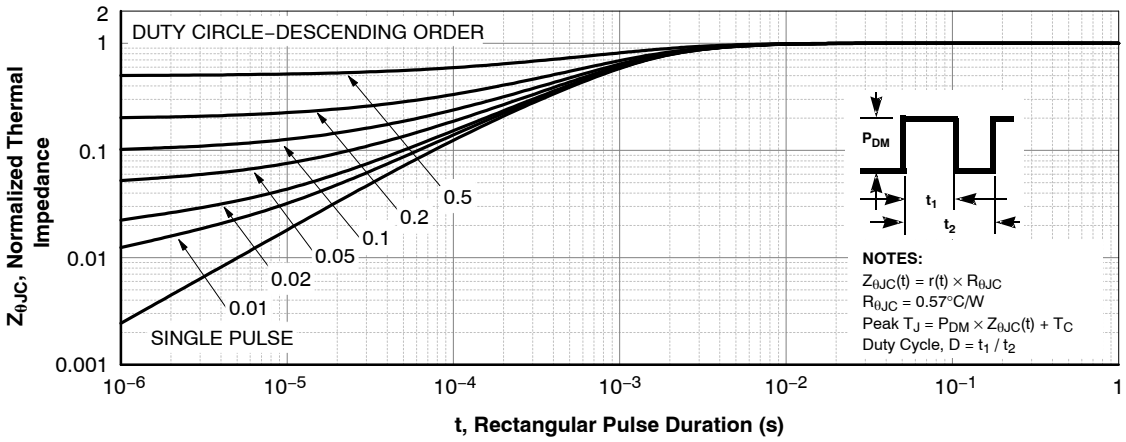


Figure 9. Junction−to−Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

L = 0.5 mH
R < 0.1 Ω
V_{DD} = 50 V
EAVL = 1/2LI2 [$V_{R(AVL)}$ / ($V_{R(AVL)}$ − V_{DD})]
Q1 = IGBT (BV_{CES} > DUT $V_{R(AVL)}$)

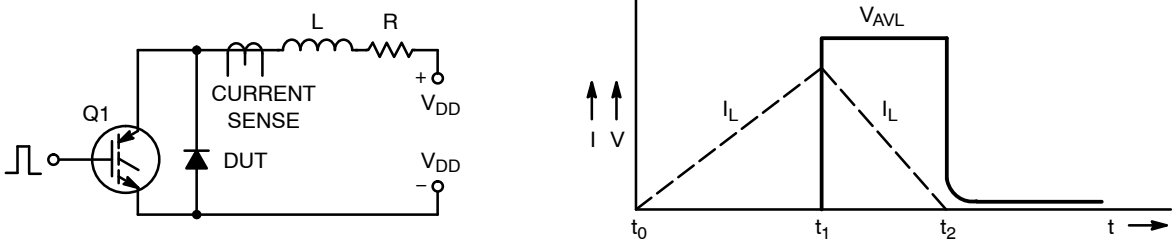
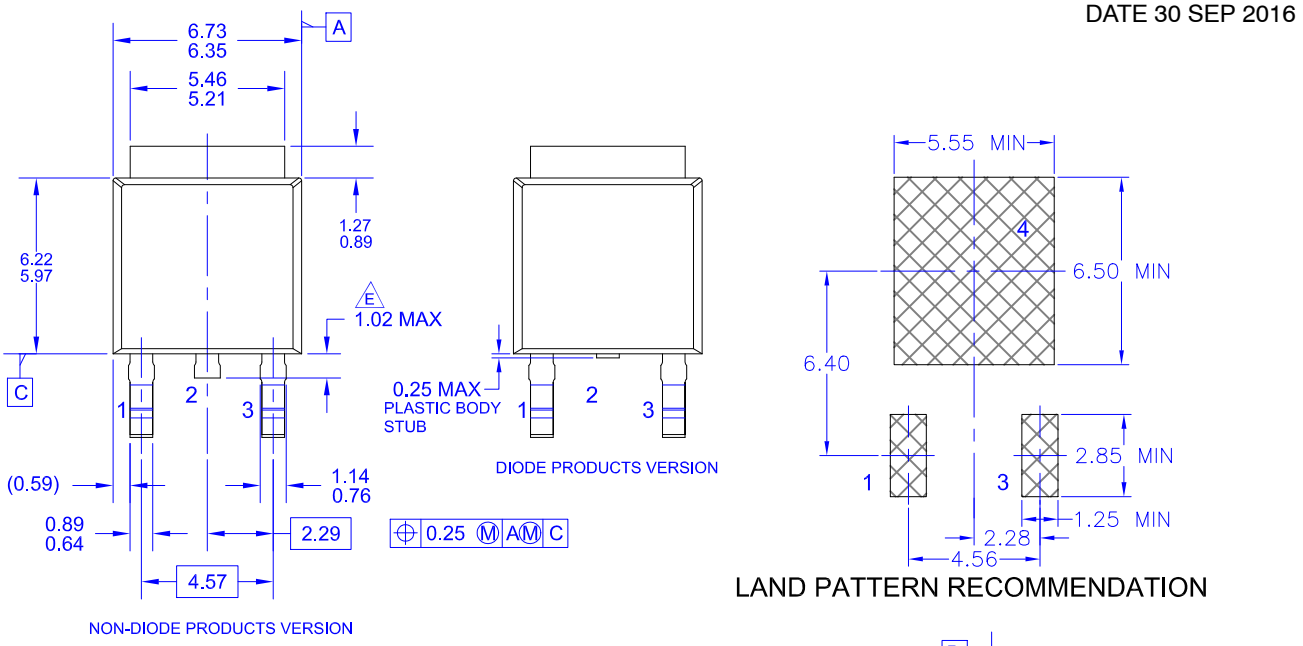
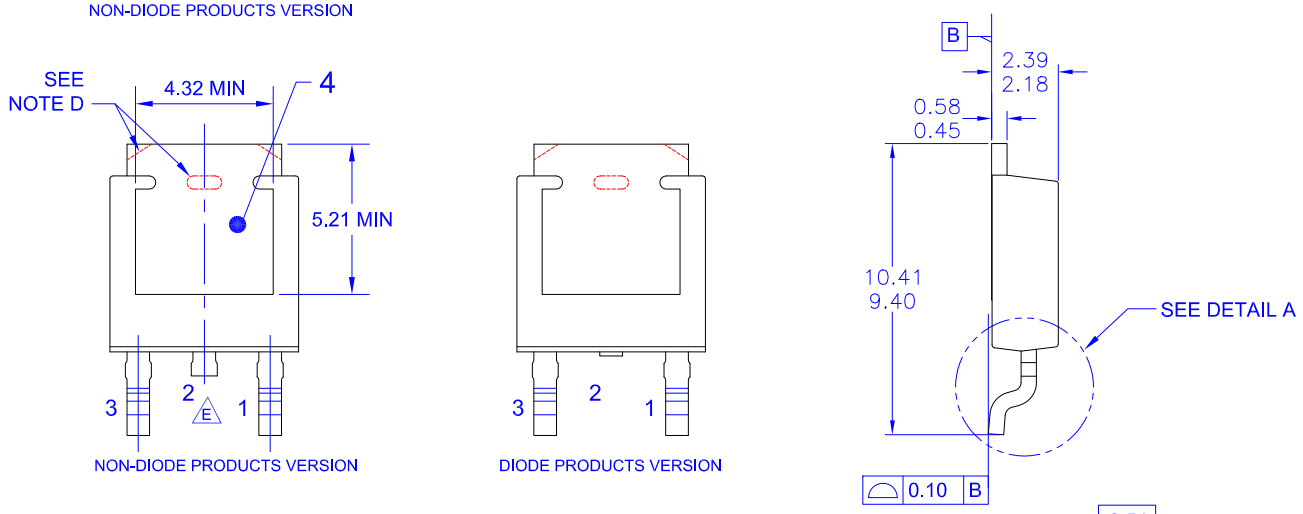


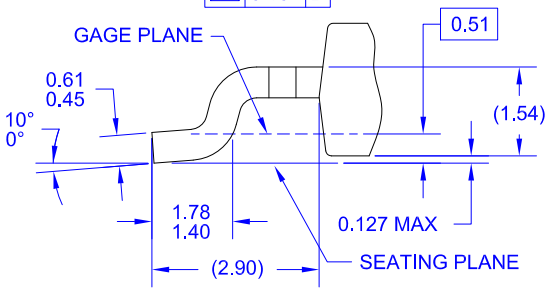
Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

DPAK3 (TO−252 3 LD)
CASE 369AS
ISSUE O

DATE 30 SEP 2016







NOTES: UNLESS OTHERWISE SPECIFIED
A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

DOCUMENT NUMBER:	**98AON13810G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**DPAK3 (TO−252 3 LD)**	**PAGE 1 OF 1**

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊